

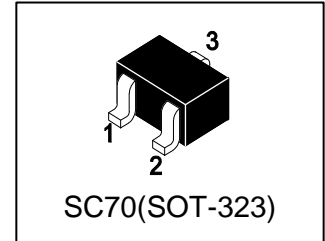
# LBC807-40WT1G

## S-LBC807-40WT1G

PNP Silicon General Purpose Transistors

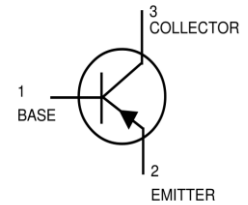
### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



### 2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBC807-40WT1G	YL	3000/Tape&Reel
LBC807-40WT3G	YL	10000/Tape&Reel



### 3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	-45	V
Collector–Base Voltage	V <sub>CBO</sub>	-50	V
Emitter–Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current(Continuous)	I <sub>C</sub>	-500	mA

### 4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation FR-5 Board (Note 1) TA = 25°C	PD	150	mW
Derate above 25°C		1.2	mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	833	°C/W
Total Device Dissipation Alumina Substrate (Note 2) TA = 25°C	PD	200	mW
Derate above 25°C		1.6	mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	625	°C/W
Junction and Storage Temperature	T <sub>J</sub> ,T <sub>stg</sub>	-55~+150	°C

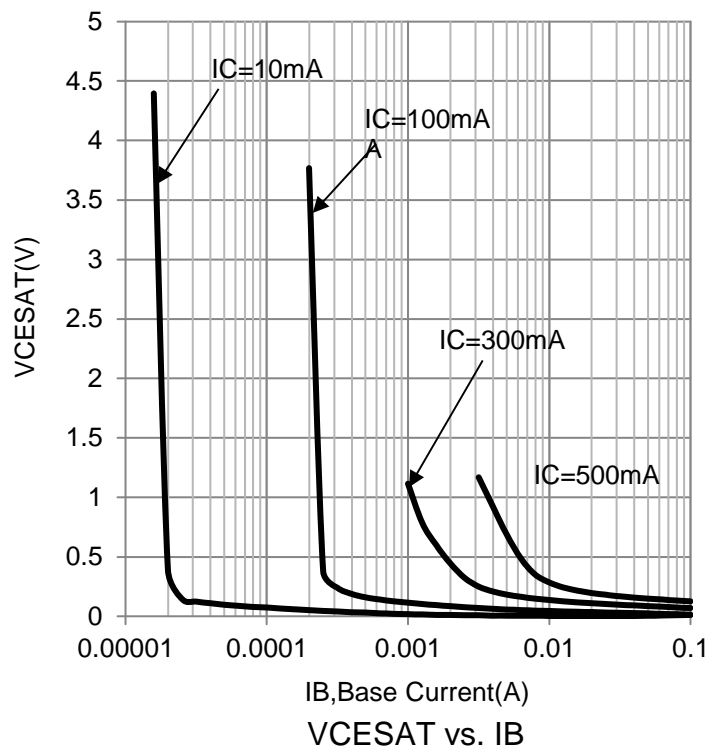
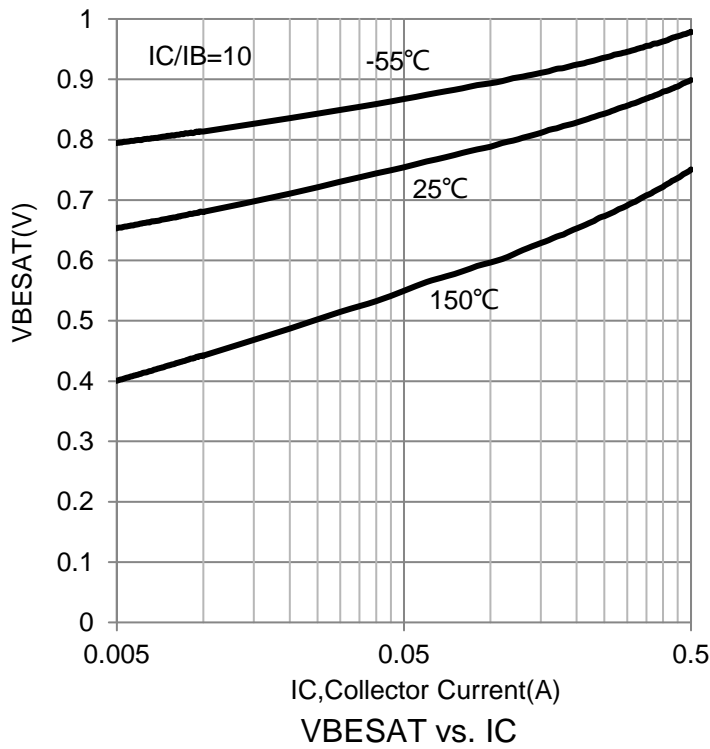
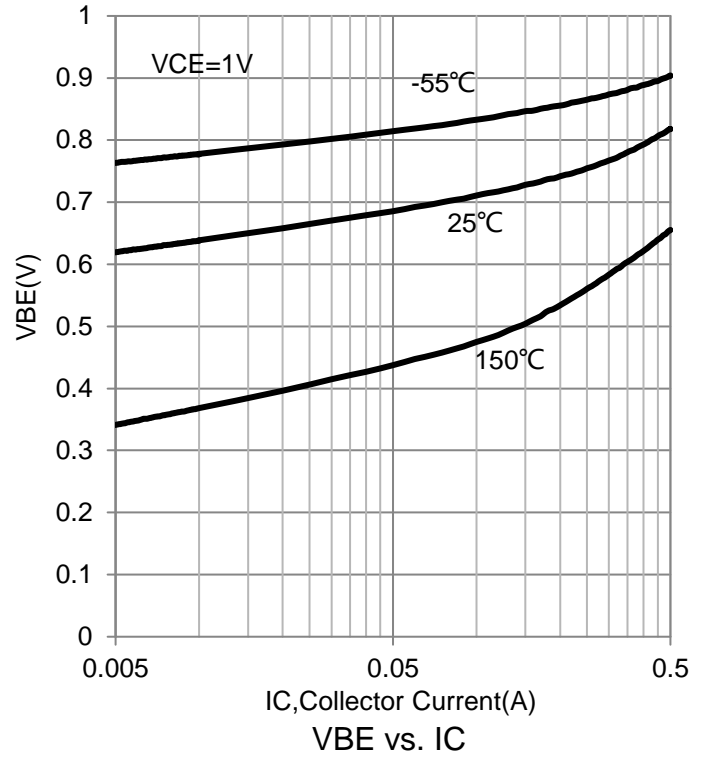
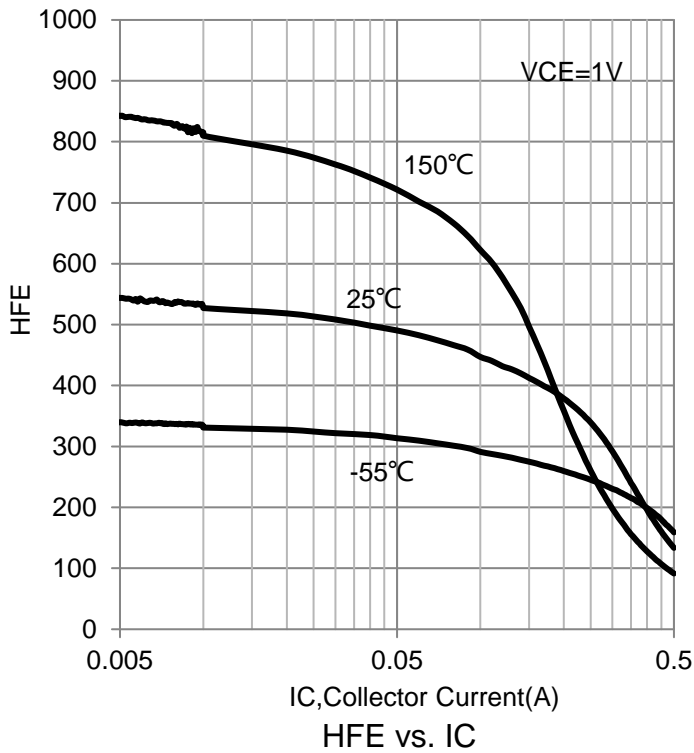
1. FR-5 = 1.0 × 0.75 × 0.062 in.

2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

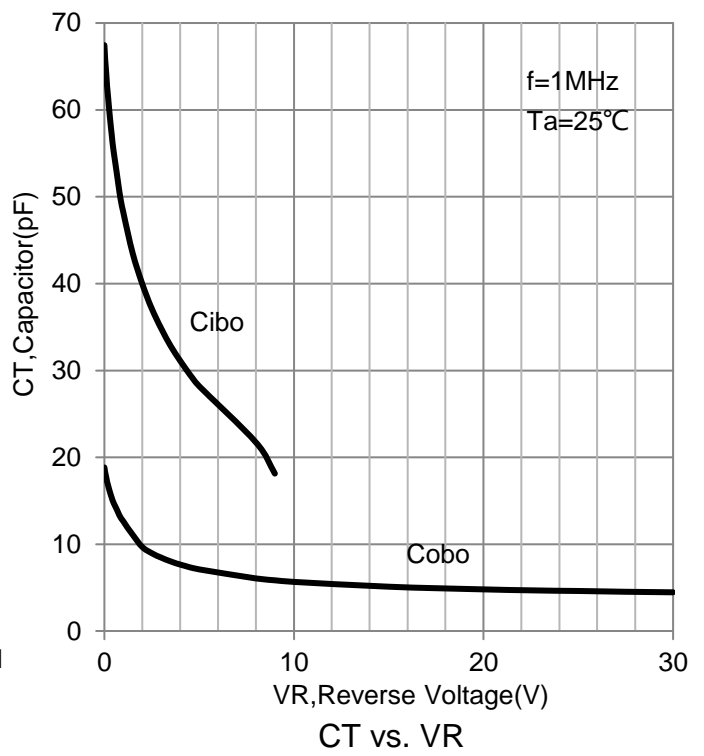
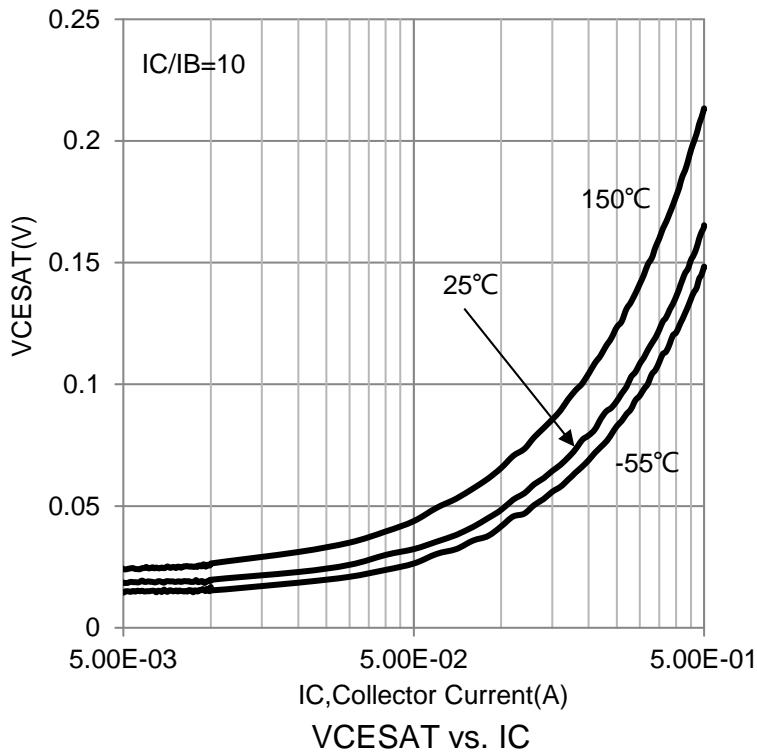
**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

Characteristic	Symbol	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage (IC = -10 mA)	V(BR)CEO	-45	-	-	V
Collector–Emitter Breakdown Voltage (IC = -10 μA, VEB = 0)	V(BR)CES	-50	-	-	V
Emitter–Base Breakdown Voltage (IE = -1.0 μA)	V(BR)EBO	-5	-	-	V
Collector Cutoff Current (VCB = -20 V) (VCB = -20 V, TA= 150°C)	ICBO	-	-	-100 -5	nA μA
<b>ON CHARACTERISTICS</b>					
DC Current Gain (IC = -100 mA, VCE = -1.0 V) (IC = -500 mA, VCE = -1.0 V)	hFE	250 40	- -	600 -	
Collector–Emitter Saturation Voltage (IC = -500 mA, IB = -50 mA)	VCE(sat)	-	-	-0.7	V
Base–Emitter Voltage (IC = -500 mA, VCE = -1.0 V)	VBE(on)	-	-	-1.2	V
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Current–Gain — Bandwidth Product (IC = -10 mA, VCE = -5.0 V, f = 100 MHz)	fT	100	-	-	MHz
Output Capacitance (VCB = -10 V, f = 1.0 MHz)	Cobo	-	10	-	pF

**6. ELECTRICAL CHARACTERISTICS CURVES**



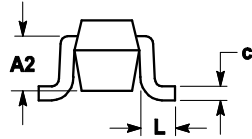
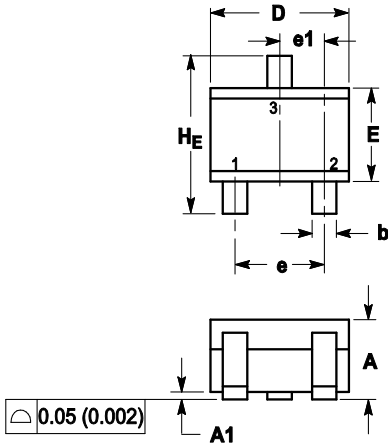
**6.ELECTRICAL CHARACTERISTICS CURVES(Con.)**



## 7. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70REF			0.028REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65REF			0.026REF		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

## 8. SOLDERING FOOTPRINT

